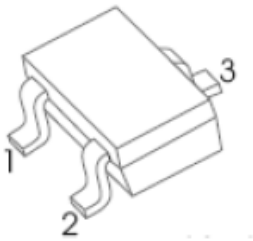
ShenzhenTaimaoTechnology Co.,Ltd.

SOT-323 Plastic-Encapsulate Diodes

BAP64-04W,05W,06W Pin Diode

SOT-323



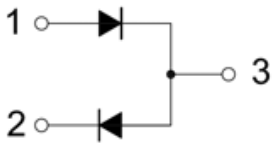
FEATURE

- High voltage ,current controlled
- RF resistor for RF attenuators and switches
- Low diode capacitance
- Low diode forward resistance
- Low series inductance
- For applications up to 3 GHz

APPLICATION

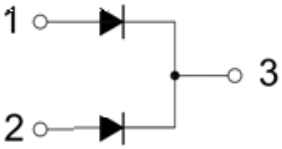
- RF attenuators and switches

BAP64-04W



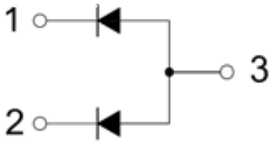
MARKING:4W

BAP64-05W



MARKING:5W

BAP64-06W



MARKING:6W

Maximum Ratings (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Value	Unit
Continuous reverse voltage	V_R	175	V
Continuous forward current	I_F	100	mA
Power dissipation	P_D	200	mW
Thermal resistance from junction to ambient	$R_{\theta JA}$	625	℃/W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-55~+150	℃

Electrical characteristic (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Forward Voltage	V_F	I_F=50mA			1.1	V
Reverse Current	I_{R1}	V_{R1}=175V			10	μA
	I_{R2}	V_{R2}=20V			1	
Diode Capacitance	C_{d1}	V_R=0V, f=1MHz		0.52		pF
	C_{d2}	V_R=1V,f=1MHz			0.5	
	C_{d3}	V_R=20V,f=1MHz			0.35	
Diode Forward Resistance (note 1)	r_{d1}	I_F=0.5mA, f=100MHz			40	Ω
	r_{d2}	I_F=1mA, f=100MHz			20	
	r_{d3}	I_F=10mA, f=100MHz			3.8	
	r_{d4}	I_F=100mA, f=100MHz			1.35	
Charge Carrier Life Time	τ_L	When switched from I_F =10mA to I_R=6mA; R_L=100Ω;measured at I_R =3mA		1.55		μs
Series Inductance	L_S	I_F=10mA, f=100MHz BAP64-04W/06W		1.6		nH
		BAP64-05W		1.4		

Note:
1.Guaranteed on AQL basis: inspection level S4,AQL 1.0.